

N-channel 100 V, 2.3 mΩ typ., 180 A STripFET™ VII DeepGATE™ Power MOSFET in a TO-220 package

Datasheet - production data

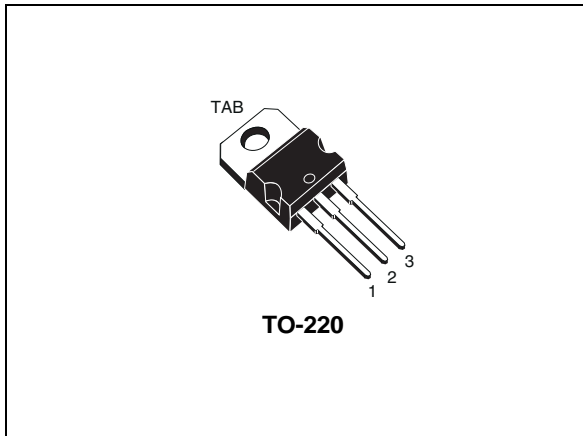
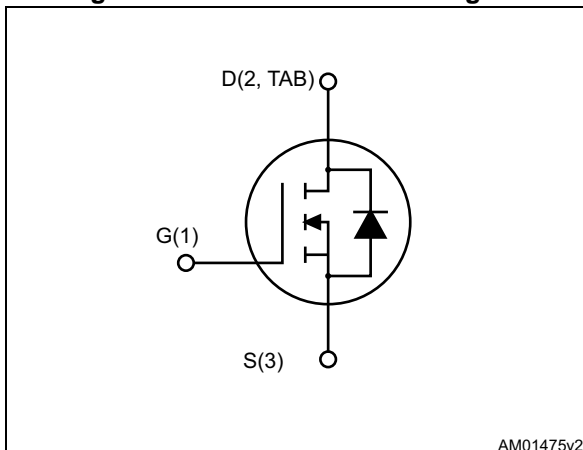


Figure 1. Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STP310N10F7	100 V	2.7 mΩ	180 A

- Ultra low on-resistance
- 100% avalanche tested

Applications

- Switching applications

Description

This device utilizes the 7th generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STP310N10F7	310N10F7	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C=100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	315	W
	Derating factor	2.1	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy ($T_J = 25^\circ\text{C}$, $L=0.55\text{ mH}$, $I_{AS}=65\text{ A}$)	1	J
T_j T_{stg}	Operating junction temperature storage temperature	- 55 to 175	$^\circ\text{C}$

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting $T_J=25^\circ\text{C}$, $I_D=60\text{ A}$, $V_{DD}=50\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.48	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\ \mu\text{A}$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 100\ \text{V}$			1	μA
		$V_{DS} = 100\ \text{V}$, $T_C = 125\text{°C}$			100	μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = 20\ \text{V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2.5	3.5	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}$, $I_D = 60\ \text{A}$		2.3	2.7	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0$	-	12800	-	pF
C_{oss}	Output capacitance		-	3500	-	pF
C_{rss}	Reverse transfer capacitance		-	170	-	pF
Q_g	Total gate charge	$V_{DD} = 50\ \text{V}$, $I_D = 180\ \text{A}$, $V_{GS} = 10\ \text{V}$ (see Figure 14)	-	180	-	nC
Q_{gs}	Gate-source charge		-	78	-	nC
Q_{gd}	Gate-source charge		-	34	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ \text{V}$, $I_D = 90\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ \text{V}$ (see Figure 13 , Figure 18)	-	62	-	ns
t_r	Rise time		-	108	-	ns
$t_{d(off)}$	Turn-off delay time		-	148	-	ns
t_f	Fall time		-	40	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		180	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		720	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=60\text{ A}$, $V_{GS}=0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD}=180\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=80\text{ V}$, $T_j=150^\circ\text{C}$ (see Figure 15)	-	85		ns
Q_{rr}	Reverse recovery charge		-	200		nC
I_{RRM}	Reverse recovery current		-	4.7		A

1. Pulse width limited by safe operating area.

2. Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

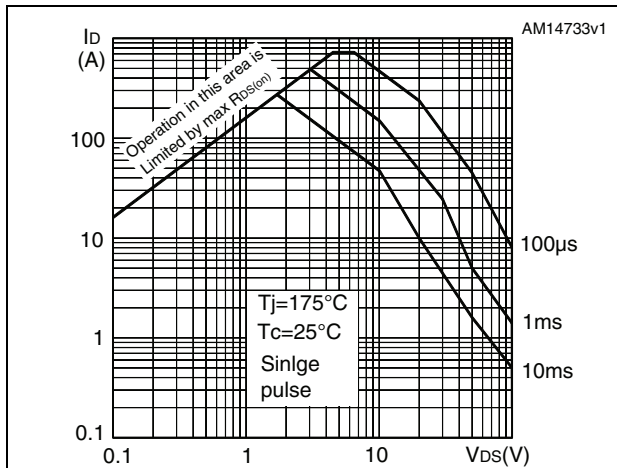


Figure 3. Thermal impedance

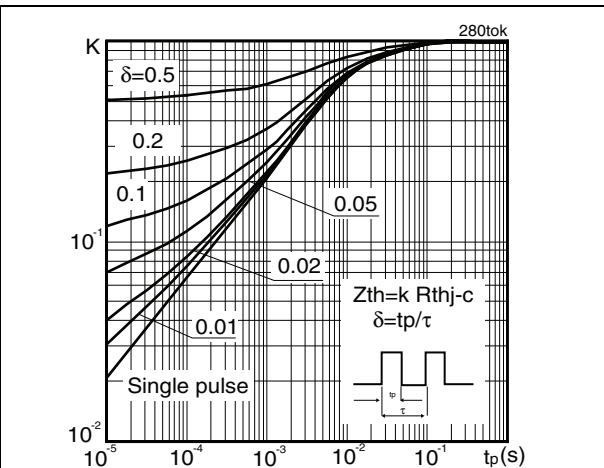


Figure 4. Output characteristics

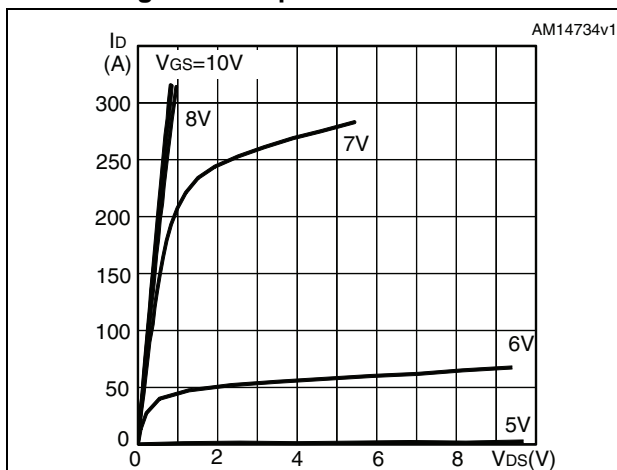


Figure 5. Transfer characteristics

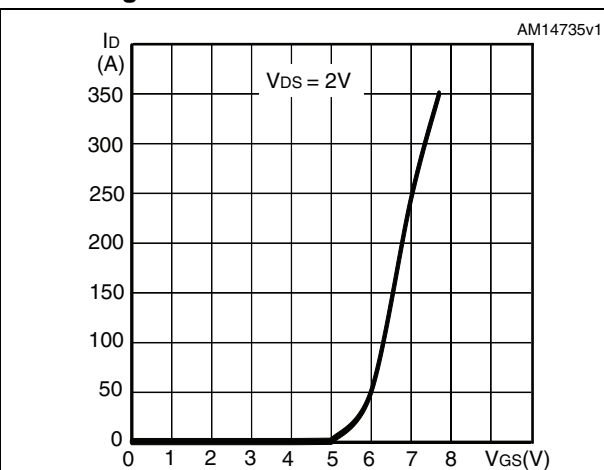


Figure 6. Gate charge vs gate-source voltage

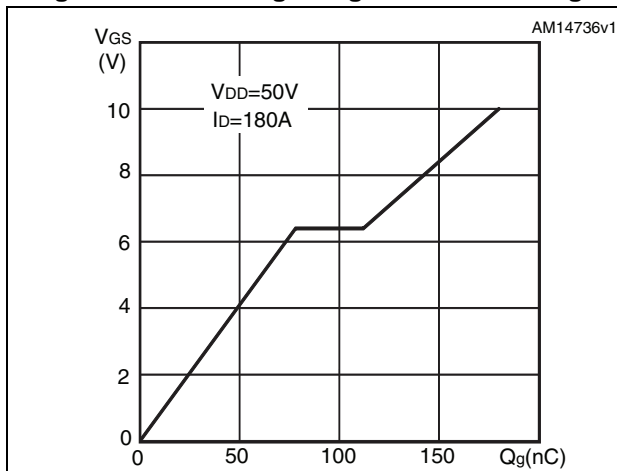


Figure 7. Static drain-source on-resistance

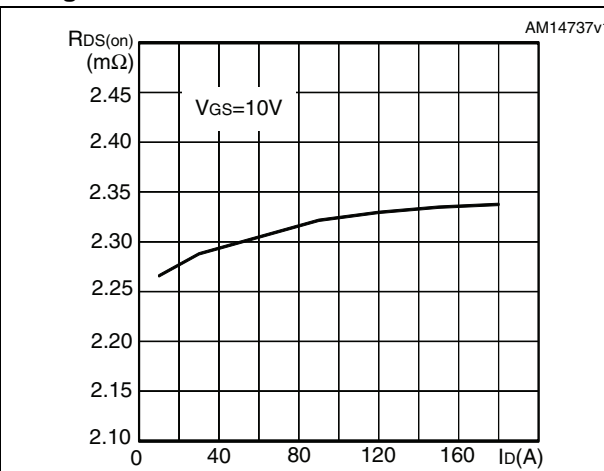


Figure 8. Capacitance variations

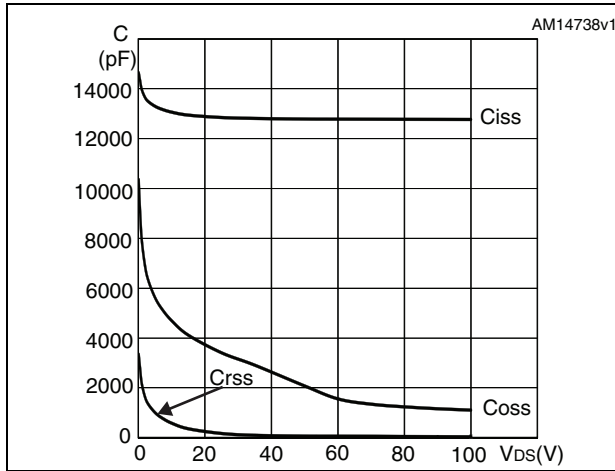


Figure 9. Source-drain diode forward characteristics

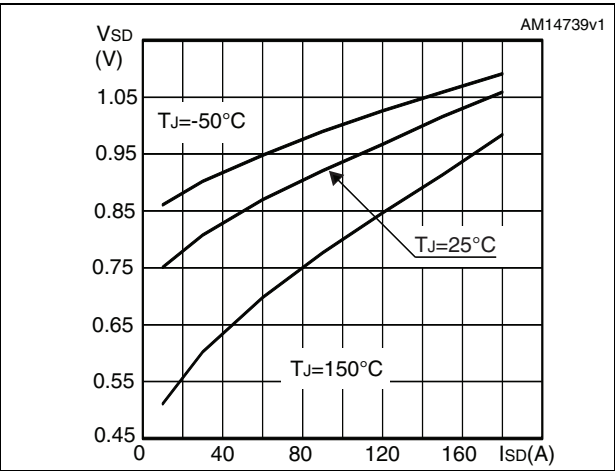


Figure 10. Normalized gate threshold voltage vs temperature

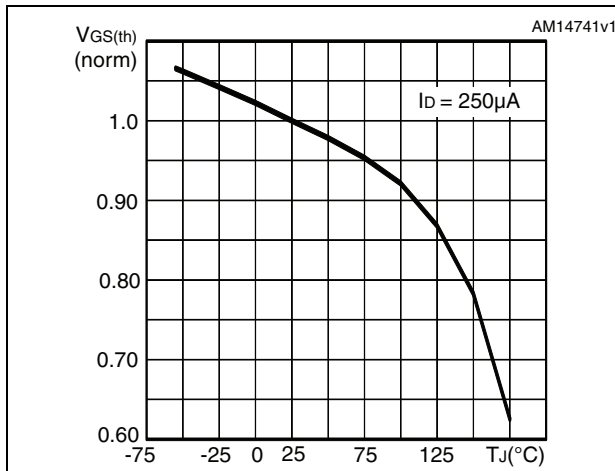


Figure 11. Normalized on-resistance vs temperature

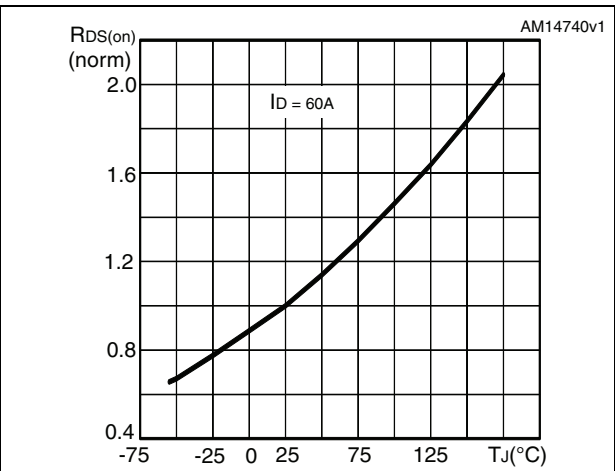
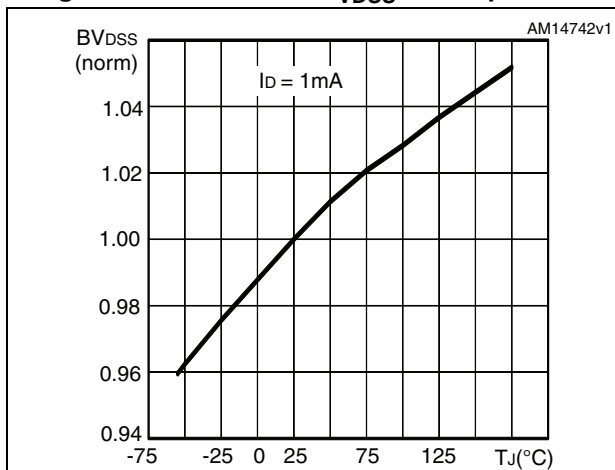


Figure 12. Normalized BV_{DSS} vs temperature



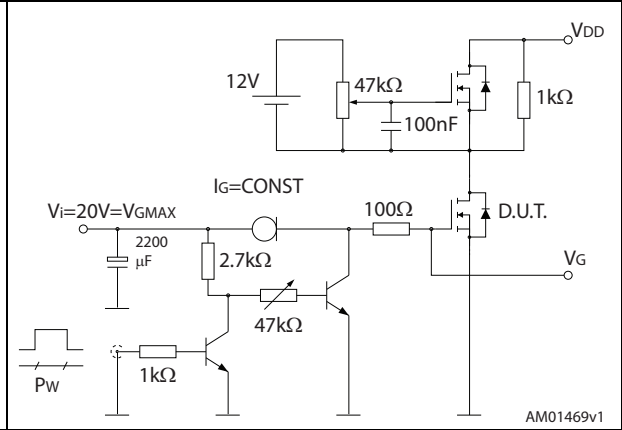
3 Test circuits

Figure 13. Switching times test circuit for resistive load



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Figure 14. Gate charge test circuit



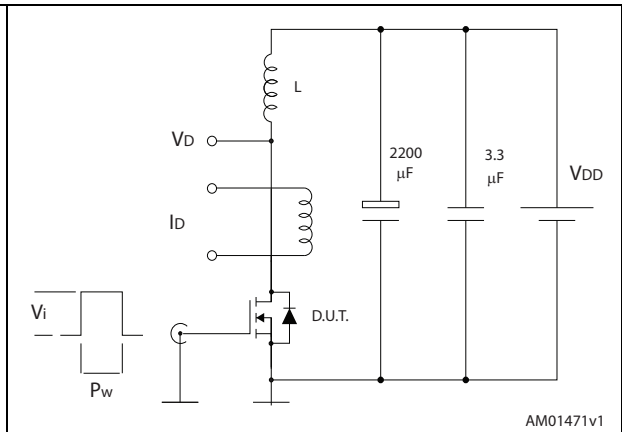
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Figure 15. Test circuit for inductive load switching and diode recovery times



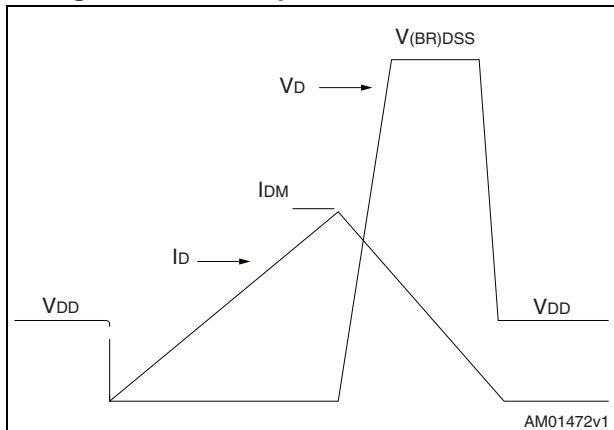
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Figure 16. Unclamped inductive load test circuit



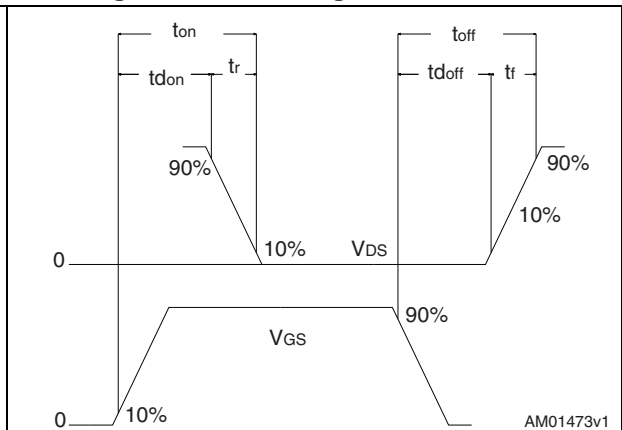
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform



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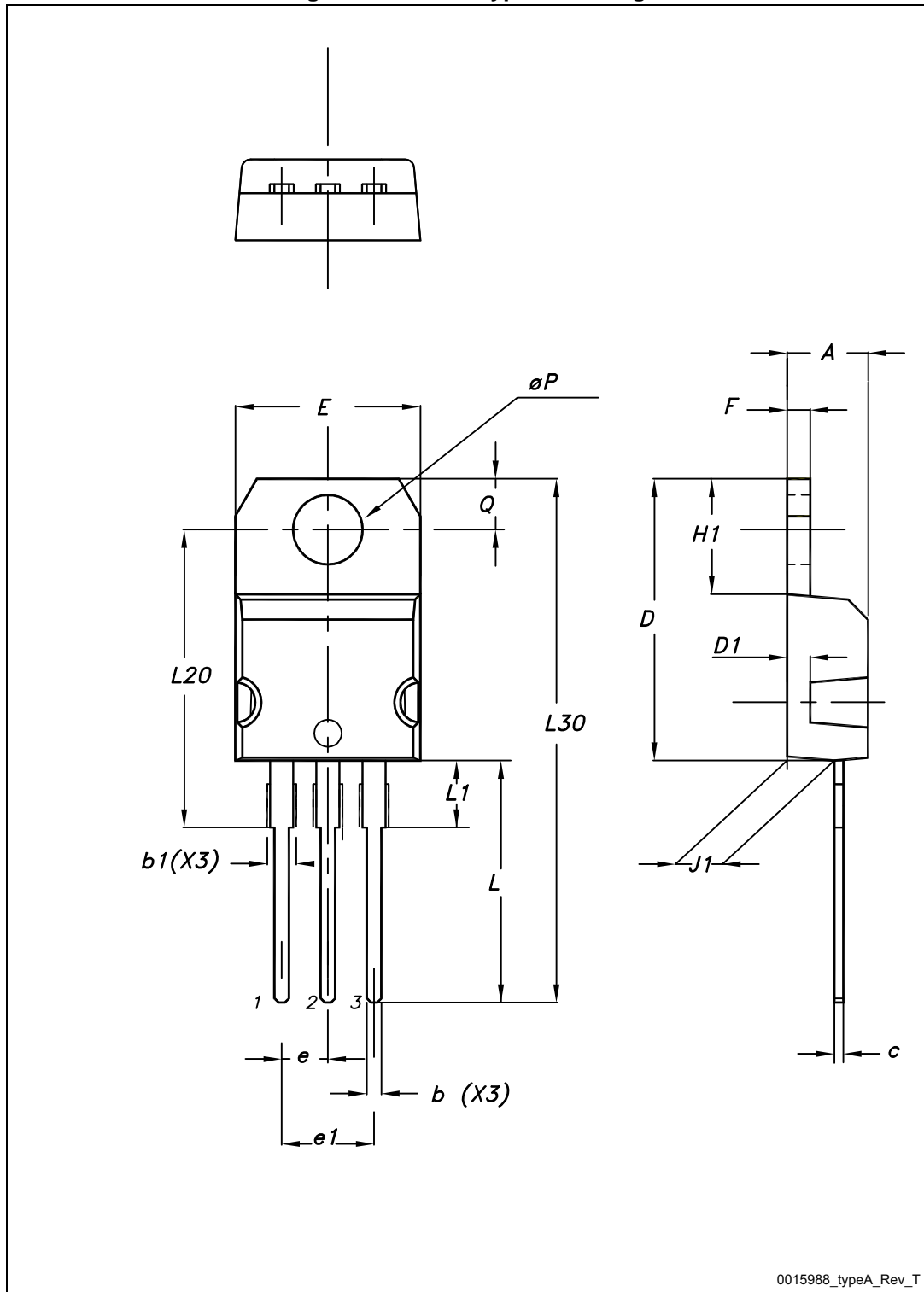
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



0015988_typeA_Rev_T

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
19-Oct-2011	1	Initial version.
21-Dec-2011	2	Updated title and description in cover page.
06-Mar-2012	3	Updated I_D value at $T_C = 25^\circ\text{C}$ in the whole document. Table 5 , Table 6 and Table 7 have been updated with typical values.
20-Aug-2012	4	Document status promoted from preliminary to production data. Added Section 2.1: Electrical characteristics (curves) . Minor text changes.
31-Oct-2012	5	– Added: H ² PAK-2 and H ² PAK-6 packages – Updated: Section 4: Package mechanical data and Section 4: Package mechanical data – Minor text changes
07-Dec-2012	6	– Minor text changes – The part numbers STH310N10F7-2, STH310N10F7-6 have been moved to a separate datasheet
31-Jul-2013	7	– Modified: I_{DSS} and $V_{GS(th)}$ values in Table 4 . – Minor text changes – Inserted: E_{AS} value in Table 2

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